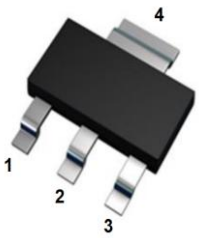
LBTP660Z4TZHG
S-LBTP660Z4TZHG

General Purpose Transistors PNP Silicon



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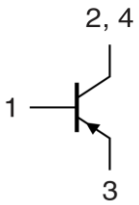


1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S-prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBTP660Z4TZHG	A9	1000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25ºC)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	VCEO	-60	V
Collector–Base Voltage	VCBO	-100	V
Emitter–Base Voltage	VEBO	-6	V
Collector Current — Continuous	IC	-6	A
Peak collector current	ICM	-12	A
Junction and Storage temperature	TJ,Tstg	−55~+150	ºC

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR−4 Board (Note 1) @ TA = 25ºC	PD	833	mW
Thermal Resistance, Junction–to–Ambient(Note 1)	RΘJA	150	ºC/W

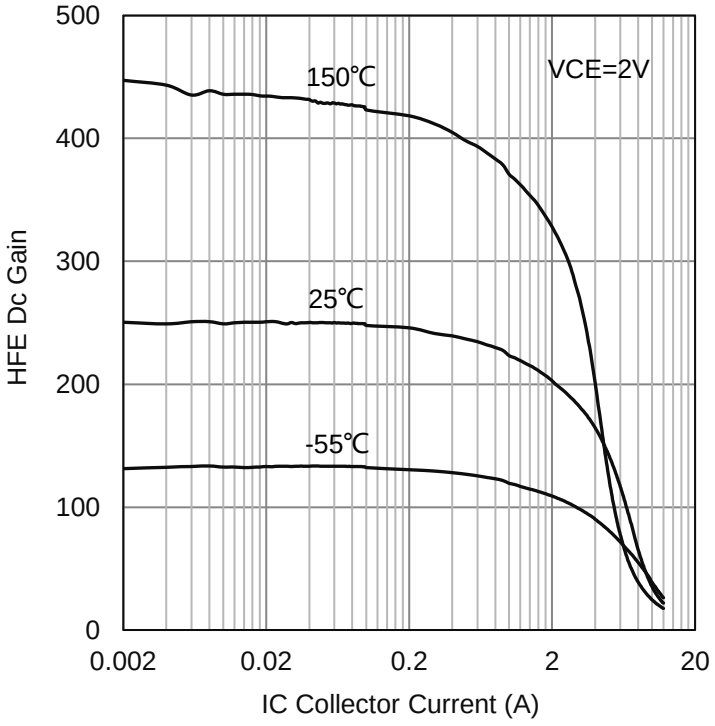
1. FR–4 = 30.0mm×25.0mm×1.6mm.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

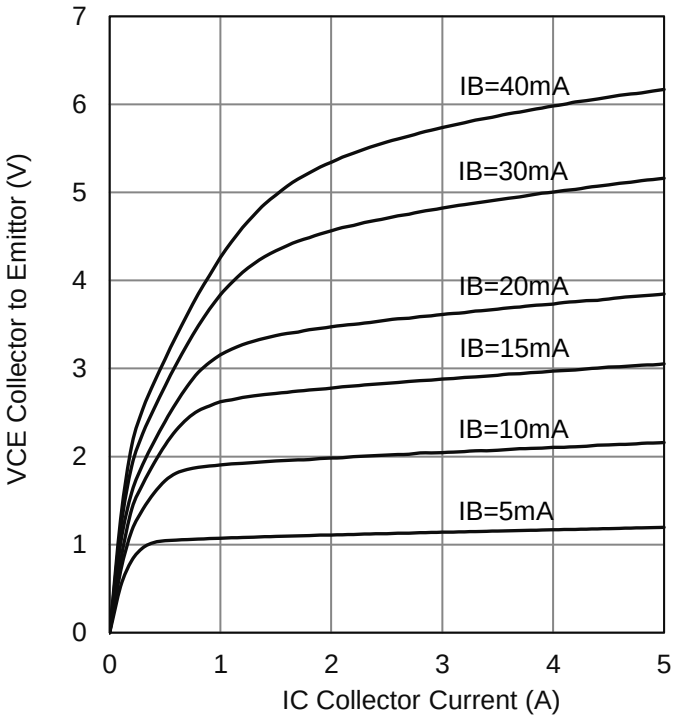
Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage (IC=-10mA,IB=0)	VBR(CEO)	-60	-	-	V
Collector–Base Breakdown Voltage (IC=-100μA,IE=0)	VBR(CBO)	-100	-	-	V
Emitter–Base Breakdown Voltage (IE=-100μA,IC=0)	VBR(EBO)	-6	-	-	V
Collector-Base cut-off current (VCB = -100 V, IE = 0)	ICBO	-	-	-100	nA
Emitter-Base cut-off current (VEB =-6V, IC =0)	IEBO	-	-	-100	nA
Collector-Emitter cutoff Current (IB=0, VCE = -60V)	ICEO	-	-	-10	μA
DC Current Gain (VCE = -2 V,IC = -500mA) (VCE = -2 V,IC = -1A) (VCE = -2 V,IC = -2A) (VCE = -2 V,IC = -6A)	HFE	 150 120 100 70	 - - - -	 - 360 - -	
Collector–Emitter Saturation Voltage (IC=-100mA,IB=-2mA) (IC=-1A,IB=-100mA) (IC=-2A,IB=-200mA) (IC=-3A,IB=-300mA) (IC=-6A,IB=-600mA)	VCE(sat)	 - - - - -	 - - - - -	 -50 -70 -120 -250 -350	mV
Base-Emitter saturation voltage(Note 2) (IC=-1A, IB=-100mA)	VBE(sat)	-	-	-1	V
Transition Frequency (VCE = -10 V, IC = -500 mA,f = 1 MHz)	fT	100	-	-	MHz
Input Capacitance (VEB = -5.0 V, f = 1.0 MHz)	Cibo	-	360	-	pF
Output Capacitance (VCB = -10 V, f = 1.0 MHz)	Cobo	-	60	-	pF

2.tp ⩽ 300 μs,δ ⩽ 0.02;

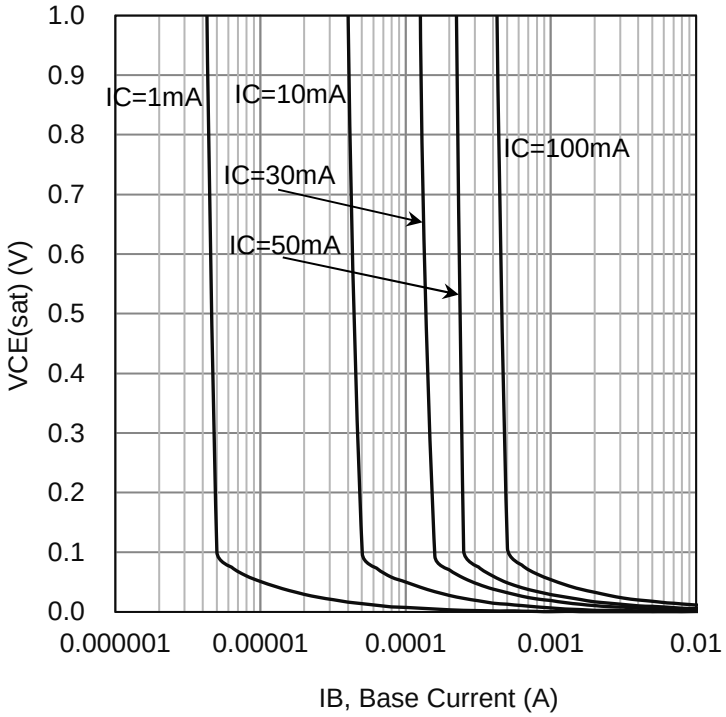
6.ELECTRICAL CHARACTERISTICS CURVES



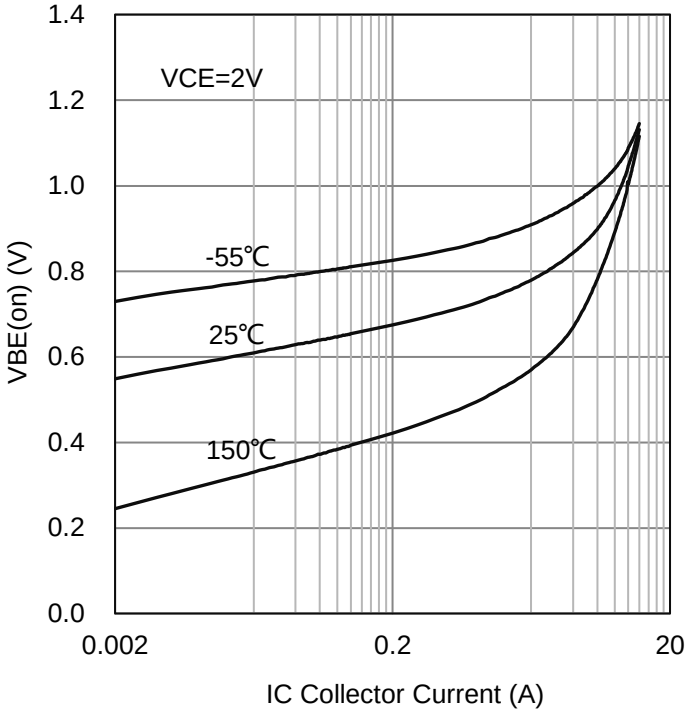
HFE vs. IC



IC vs. VCE

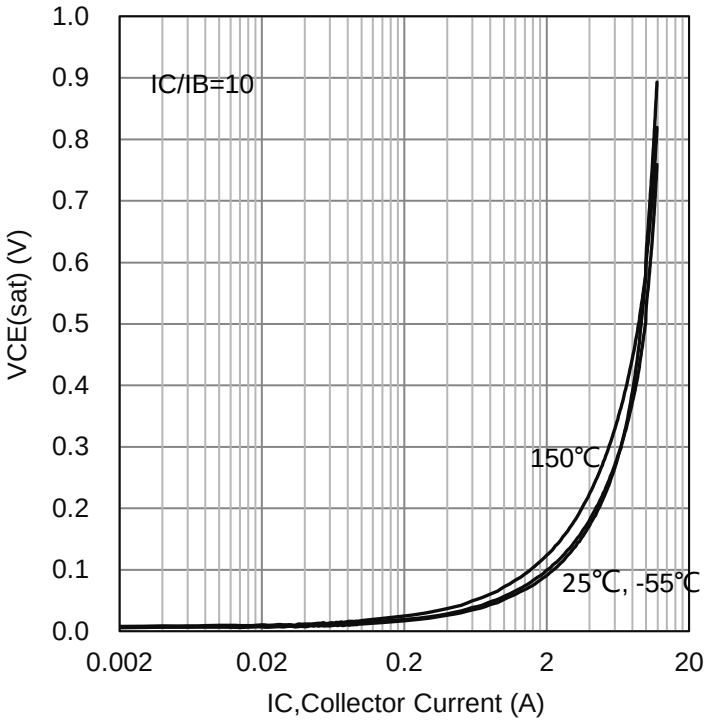


VCE(sat) vs. IB

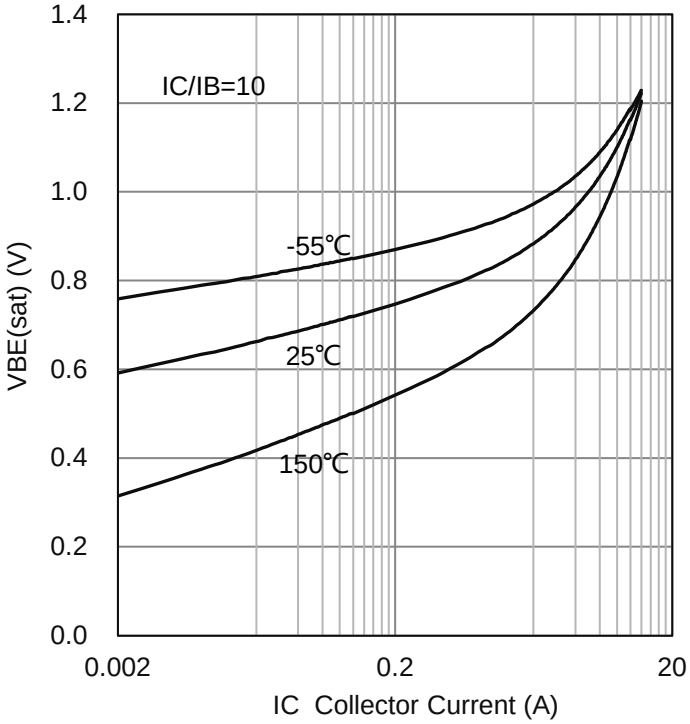


VBE(on) vs. IC

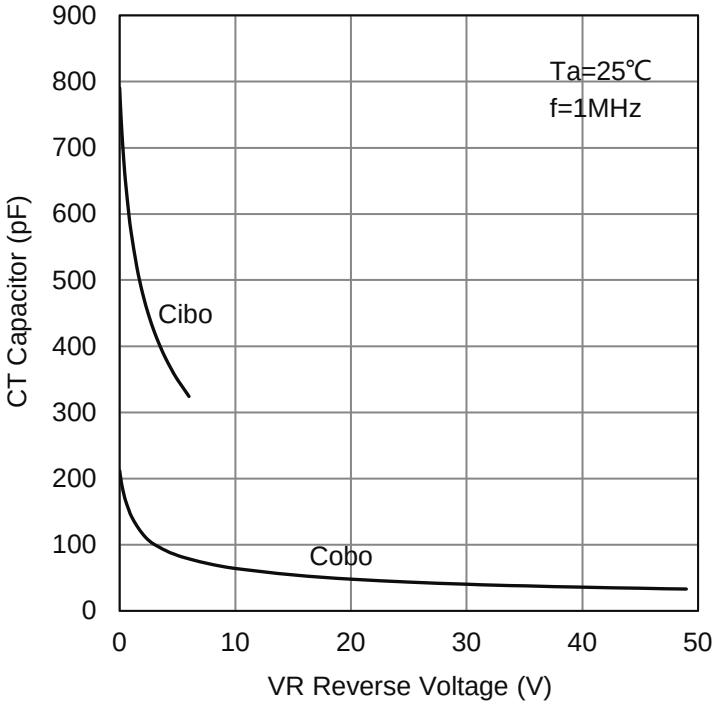
6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



VCE(sat) vs. IC



VBE(sat) vs. IC



CT vs. VR

7.OUTLINE AND DIMENSIONS

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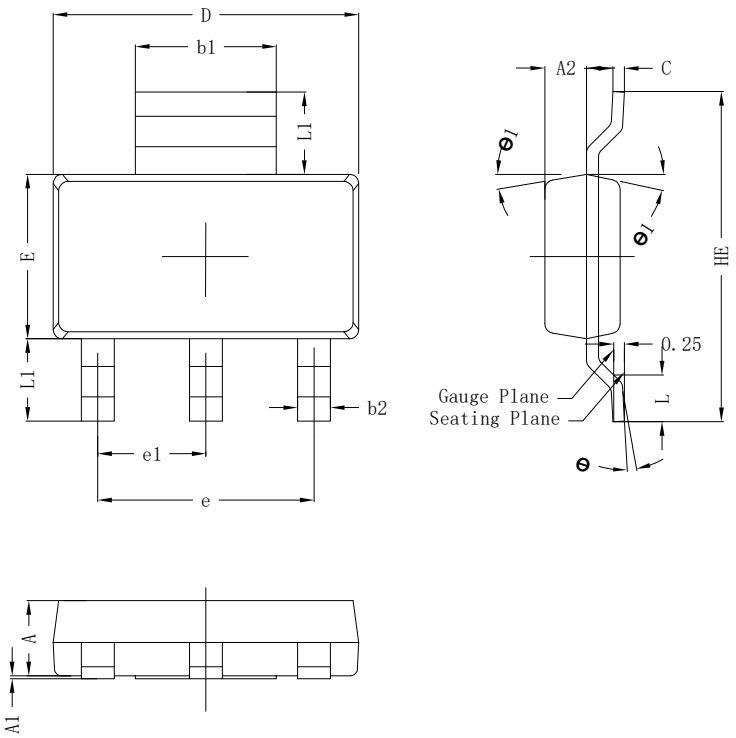

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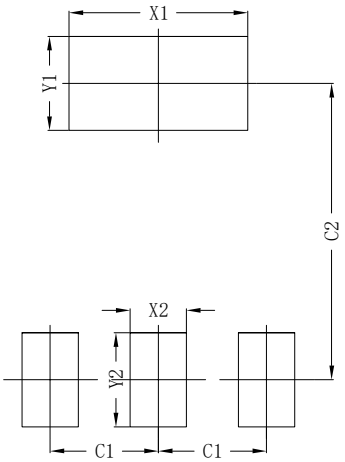
DIM	MIN	NOR	MAX
A	1.50	1.60	1.70
A1	0.00	0.05	0.10
A2	0.80	0.90	1.00
b1	2.90	3.02	3.10
b2	0.60	0.72	0.80
c	0.20	0.27	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	4.60BSC		
e1	2.30BSC		
HE	6.80	7.00	7.20
L	0.80	1.00	1.20
L1	1.75(REF)		
θ	0°~8°		
θ 1	8°	10°	12°
All Dimensions in mm			

GENERAL NOTES

1. Top package surface finish Ra0.4±0.2um
2. Bottom package surface finish Ra0.7±0.2um
3. Side package surface finish Ra0.4±0.2um
4. Protrusion or Gate Burrs shall not exceed 0.10mm per side.

8.SOLDERING FOOTPRINT



SOT223	
DIM	(mm)
X1	3.80
Y1	2.00
X2	1.20
Y2	2.00
C1	2.30
C2	6.30

DISCLAIMER

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